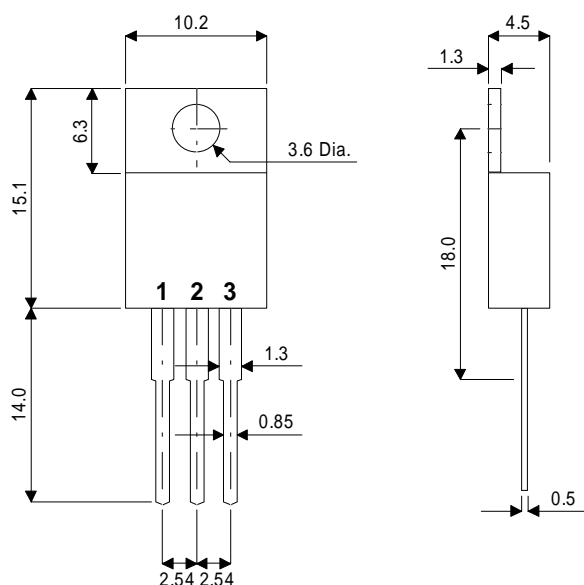


**MECHANICAL DATA**

Dimensions in mm



**TO220**

Pin 1 – Base

Pin 2 – Collector

Pin 3 – Emitter

**ADVANCED  
DISTRIBUTED BASE DESIGN  
HIGH VOLTAGE  
HIGH SPEED NPN  
SILICON POWER TRANSISTOR**

Designed for use in  
electronic ballast applications

- SEMEFAB DESIGNED AND DIFFUSED DIE
- HIGH VOLTAGE
- FAST SWITCHING
- HIGH ENERGY RATING

**FEATURES**

- Multi-base for efficient energy distribution across the chip resulting in significantly improved switching and energy ratings across full temperature range.
- Ion implant and high accuracy masking for tight control of characteristics from batch to batch.
- Triple Guard Rings for improved control of high voltages.

**ABSOLUTE MAXIMUM RATINGS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

$V_{CBO}$	Collector – Base Voltage ( $I_E=0$ )	500V
$V_{CEO}$	Collector – Emitter Voltage ( $I_B = 0$ )	250V
$V_{EBO}$	Emitter – Base Voltage ( $I_C = 0$ )	10V
$I_C$	Continuous Collector Current	12A
$I_{C(PK)}$	Peak Collector Current	24A
$I_B$	Base Current	4A
$P_{tot}$	Total Dissipation at $T_{case} = 25^{\circ}C$	90W
$T_{stg}$	Operating and Storage Temperature Range	-55 to +150°C

**ELECTRICAL CHARACTERISTICS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit		
<b>ELECTRICAL CHARACTERISTICS</b>							
$V_{CEO(sus)}$	Collector – Emitter Sustaining Voltage	$I_C = 10mA$	250		V		
$V_{(BR)CBO}$	Collector – Base Breakdown Voltage	$I_C = 1mA$	500				
$V_{(BR)EBO}$	Emitter – Base Breakdown Voltage	$I_E = 1mA$	10				
$I_{CBO}$	Collector – Base Cut-Off Current	$V_{CB} = 500V$		10	$\mu A$		
			$T_C = 125^{\circ}C$	100			
$I_{CEO}$	Collector – Emitter Cut-Off Current	$I_B = 0$	$V_{CE} = 240V$	100	$\mu A$		
$I_{EBO}$	Emitter Cut-Off Current	$V_{EB} = 9V$	$I_C = 0$		10		
				$T_C = 125^{\circ}C$	100		
$h_{FE}^*$	DC Current Gain	$I_C = 0.1A$	$V_{CE} = 5V$	20	30	—	
		$I_C = 1A$	$V_{CE} = 5V$	25	50		
		$I_C = 7A$	$V_{CE} = 1V$	5	9		
			$T_C = 125^{\circ}C$	4	8		
$V_{CE(sat)}^*$	Collector – Emitter Saturation Voltage	$I_C = 1A$	$I_B = 0.2A$		0.07	0.1	V
		$I_C = 4A$	$I_B = 0.8A$		0.2	0.5	
		$I_C = 7A$	$I_B = 1.4A$		0.4	0.8	
$V_{BE(sat)}^*$	Base – Emitter Saturation Voltage	$I_C = 4A$	$I_B = 0.8A$		0.9	1.2	V
		$I_C = 7A$	$I_B = 1.4A$		1.1	1.4	
<b>DYNAMIC CHARACTERISTICS</b>							
$f_t$	Transition Frequency	$I_C = 0.2A$	$V_{CE} = 4V$		20	MHz	
$C_{ob}$	Output Capacitance	$V_{CB} = 10V$	$f = 1MHz$		60	pF	

\* Pulse test  $t_p = 300\mu s$ ,  $\delta < 2\%$